Erratum: Bond-length variation in $In_xGa_{1-x}As/InP$ strained epitaxial layers [Phys. Rev. B 57, 14 619 (1998)]

F. Romanato, D. De Salvador, M. Berti, A. Drigo, M. Natali, M. Tormen, G. Rossetto, S. Pascarelli, F. Boscherini, C. Lamberti, and S. Mobilio

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We point out an important reference by Woicik *et al.*[1] concerning the bond-length distortions in mismatched heterostructures. By measuring the In-As bond length in a $Ga_{0.78}In_{0.22}As$ layer grown coherently on GaAs(001), they reached conclusions that can be compared to ours.

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[1] J. C. Woicik, J. G. Pellegrino, B. Steiner, K. E. Miyano, S. G. Bompadre, L. B. Sorensen, T.-L. Lee, and S. Khalid, Phys. Rev. Lett. **79**, 5026 (1997).

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